

FEATURES

Broadband RF port: LF to 500 MHz

Conversion gain: 3 dB

Noise figure: 12 dB

Input IP₃: 24 dBm

Input P_{1dB}: 8.5 dBm

LO drive: 0 dBm

External control of mixer bias for low power operation

Single-ended, 50 Ω LO input ports

High Input Impedance RF port

Single-supply operation: 5 V @ 97 mA

Power-down mode

Exposed paddle LFCSP: 3 mm × 3 mm

APPLICATIONS

Cellular base station receivers and transmitters

ISM receivers and transmitters

Radio links

RF Instrumentation

GENERAL DESCRIPTION

The AD8342 is a high performance, broadband active mixer. It is well suited for demanding receive applications that require wide bandwidth on all ports and very low intermodulation distortion and noise figure.

The AD8342 provides a typical conversion gain of 3dB at 500 MHz. The integrated LO driver supports a 50 Ω input impedance with a low LO drive level, helping to minimize external component count.

The high input impedance RF port can be terminated and driven single ended or a matching network can be used for best noise or power match. The RF input accepts input signals as large as 1.7 V p-p or 8 dBm (re: 50 Ω) at P_{1dB}.

FUNCTIONAL BLOCK DIAGRAM

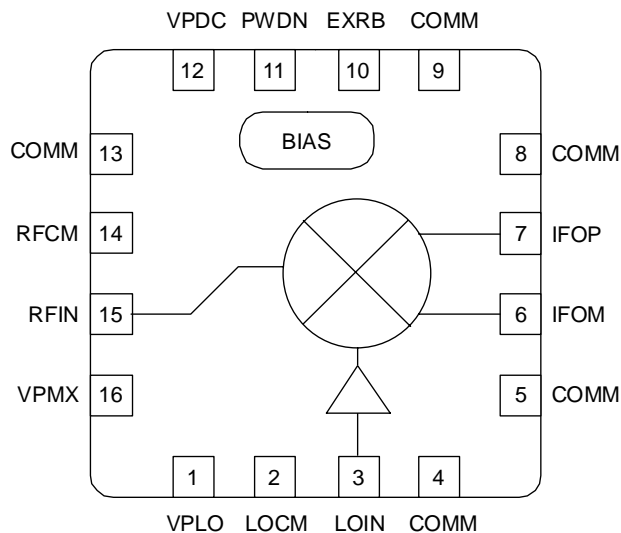


Figure 1.

The open-collector differential outputs provide excellent balance and can be used with a differential filter or IF amplifier, such as the AD8369 or AD8351. These outputs may also be converted to a single-ended signal through the use of a matching network or a transformer (balun). When centered on the VPOS supply voltage, each of the differential outputs may swing 2.5 V p-p.

The AD8342 is fabricated on an Analog Devices proprietary, high performance SiGe IC process. The AD8342 is available in a 16-lead LFCSP package. It operates over a -40°C to +85°C temperature range. An evaluation board is also available.

Rev. PrB

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SPECIFICATIONS

$V_S = 5\text{ V}$, $T_A = 25^\circ\text{C}$, $f_{RF} = 500\text{ MHz}$, $f_{LO} = 600\text{ MHz}$, LO power = 0 dBm, $Z_O = 50\ \Omega$, $R_{BIAS} = 1.82\text{ k}\Omega$, unless otherwise noted.

Table 1.

Parameter	Conditions	Min	Typ	Max	Unit
RF INPUT INTERFACE					
Return Loss	(Pin 15, RFIN and Pin 14, RFCM) Hi-Z input terminated off-chip		10		dB
DC Bias Level	Internally generated; port must be ac-coupled		2.5		V
OUTPUT INTERFACE					
Output Impedance	Differential impedance, $f = 200\text{ MHz}$		9 1		k Ω pF
DC Bias Voltage	Externally generated	4.75	V_S	5.25	V
Power Range	Via a 4:1 balun			+13	dBm
LO INTERFACE					
LO Power		-10	0	+4	dBm
Return Loss			10		dB
DC Bias Voltage	Internally generated; port must be ac-coupled		$V_S - 1.6$		V
POWER-DOWN INTERFACE					
PWDN Threshold			$V_S - 1.4$		V
PWDN Response Time	Device enabled, IF output to 90% of its final level		0.4		μs
	Device disabled, supply current < 5 mA		0.01		μs
PWDN Input Bias Current	Device enabled		-80		μA
	Device disabled		+100		μA
POWER SUPPLY					
Positive Supply Voltage		4.75	5	5.25	V
Quiescent Current					
VPDC	Supply current for bias cells		5		mA
VPMX, IFOP, IFOM	Supply current for mixer, $R_{BIAS} = 1.82\text{ k}\Omega$		57		mA
VPLO	Supply current for LO limiting amplifier		35		mA
Total Quiescent Current	$V_S = 5\text{ V}$	TBD	97	TBD	mA
Power-Down Current	Device disabled		500		μA

AC PERFORMANCE

$V_S = 5\text{ V}$, $T_A = 25^\circ\text{C}$, LO power = 0 dBm, $Z_O = 50\ \Omega$, $R_{BIAS} = 1.82\ \text{k}\Omega$, unless otherwise noted.

Table 2.

Parameter	Conditions	Min	Typ	Max	Unit
RF Frequency Range		LF		500	MHz
LO Frequency Range	High Side LO	LF		850	MHz
IF Frequency Range	Note: the upper "IF" is when used as an upconverter	DC		350	MHz
Conversion Gain	$f_{RF} = 460\ \text{MHz}$, $f_{LO} = 550\ \text{MHz}$, $f_{IF} = 90\ \text{MHz}$		3.2		dB
	$f_{RF} = 238\ \text{MHz}$, $f_{LO} = 286\ \text{MHz}$, $f_{IF} = 48\ \text{MHz}$		3.4		dB
SSB Noise Figure	$f_{RF} = 460\ \text{MHz}$, $f_{LO} = 550\ \text{MHz}$, $f_{IF} = 90\ \text{MHz}$		12.5		dB
	$f_{RF} = 238\ \text{MHz}$, $f_{LO} = 286\ \text{MHz}$, $f_{IF} = 48\ \text{MHz}$		12.2		dB
Input Third-Order Intercept	$f_{RF1} = 460\ \text{MHz}$, $f_{RF2} = 461\ \text{MHz}$, $f_{LO} = 550\ \text{MHz}$, $f_{IF} = 90\ \text{MHz}$, each RF tone -10 dBm		22.5		dBm
	$f_{RF1} = 238\ \text{MHz}$, $f_{RF2} = 239\ \text{MHz}$, $f_{LO} = 286\ \text{MHz}$, $f_{IF} = 45\ \text{MHz}$, each RF tone -10 dBm		23.5		dBm
Input Second-Order Intercept	$f_{RF1} = 460\ \text{MHz}$, $f_{RF2} = 480\ \text{MHz}$, $f_{LO} = 550\ \text{MHz}$, $f_{IF} = 90\ \text{MHz}$		48		dBm
	$f_{RF1} = 238\ \text{MHz}$, $f_{RF2} = 248\ \text{MHz}$, $f_{LO} = 286\ \text{MHz}$, $f_{IF} = 48\ \text{MHz}$		48		dBm
Input 1 dB Compression Point	$f_{RF} = 460\ \text{MHz}$, $f_{LO} = 550\ \text{MHz}$, $f_{IF} = 90\ \text{MHz}$		8.5		dBm
	$f_{RF} = 238\ \text{MHz}$, $f_{LO} = 286\ \text{MHz}$, $f_{IF} = 48\ \text{MHz}$		8.5		dBm
LO to IF Output Leakage	LO Power = 0 dBm, $f_{RF} = 500\ \text{MHz}$, $f_{LO} = 600\ \text{MHz}$		TBD		dBm
LO to RF Input Leakage	LO Power = 0 dBm, $f_{RF} = 500\ \text{MHz}$, $f_{LO} = 600\ \text{MHz}$		TBD		dBm
2xLO to IF Output Leakage	LO Power = 0 dBm, $f_{RF} = 500\ \text{MHz}$, $f_{LO} = 600\ \text{MHz}$		TBD		dBm
RF to IF Output Leakage	RF Power = -10 dBm, $f_{RF} = 500\ \text{MHz}$, $f_{LO} = 600\ \text{MHz}$		TBD		dBm
IF/2 Spurious	RF Power = -10 dBm, $f_{RF} = 500\ \text{MHz}$, $f_{LO} = 600\ \text{MHz}$		TBD		dBm

ABSOLUTE MAXIMUM RATINGS

Table 3.

Parameter	Rating
Supply Voltage, V_s	5.5 V
RF Input Level	12 dBm
LO Input Level	12 dBm
PWDN Pin	$V_s + 0.5$ V
IFOP, IFOM Bias Voltage	5.5 V
Minimum Resistor from EXRB to COMM	1.82 k Ω
Internal Power Dissipation	580 mW
θ_{JA}	77°C/W
Maximum Junction Temperature	125°C
Operating Temperature Range	-40°C to +85°C
Storage Temperature Range	-65°C to +150°C
Lead Temperature Range (Soldering 60 sec)	300°C

Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those indicated in the operational section of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

ESD CAUTION

ESD (electrostatic discharge) sensitive device. Electrostatic charges as high as 4000 V readily accumulate on the human body and test equipment and can discharge without detection. Although this product features proprietary ESD protection circuitry, permanent damage may occur on devices subjected to high energy electrostatic discharges. Therefore, proper ESD precautions are recommended to avoid performance degradation or loss of functionality.



PIN CONFIGURATION AND FUNCTION DESCRIPTIONS

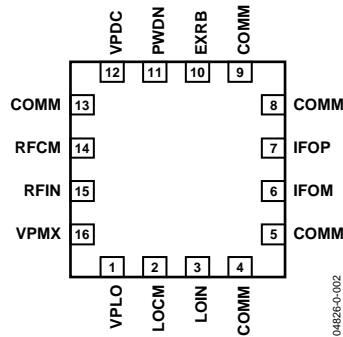


Figure 2. 16-Lead LFCSP

Table 4. Pin Function Descriptions

Pin No.	Mnemonic	Function
1	VPLO	Positive Supply Voltage for the LO Buffer: 4.75 V to 5.25 V.
2	LOCM	AC Ground for Limiting LO Amplifier, AC-Coupled to Ground.
3	LOIN	LO Input. Nominal input level 0 dBm, input level range -10 dBm to +4 dBm, re: 50 Ω, ac-coupled.
4, 5, 8, 9, 13	COMM	Device Common (DC Ground).
6, 7	IFOM, IFOP	Differential IF Outputs; Open Collectors, Each Requires DC Bias of 5.00 V (Nominal).
10	EXRB	Mixer Bias Voltage, Connect Resistor from EXRB to Ground, Typical Value of 1.82 kΩ Sets Mixer Current to Nominal Value. Minimum resistor value from EXRB to ground = 1.82 kΩ.
11	PWDN	Connect to Ground for Normal Operation. Connect pin to V_s for disable mode.
12	VPDC	Positive Supply Voltage for the DC Bias Cell: 4.75 V to 5.25 V.
14	RFCM	AC Ground for RF Input, AC-Coupled to Ground.
15	RFIN	RF Input. Must be ac-coupled.
16	VPMX	Positive Supply Voltage for the Mixer: 4.75 V to 5.25 V.

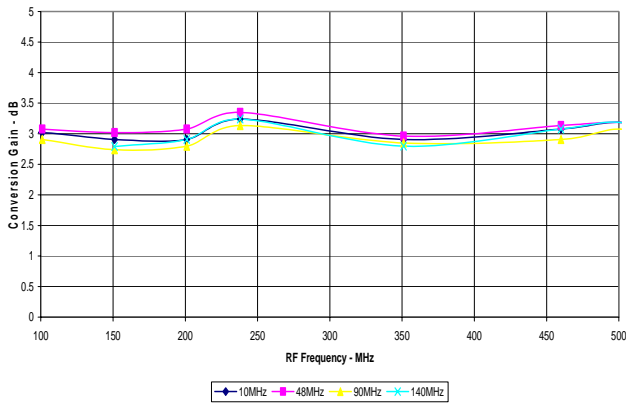


Figure 3. Conversion Gain vs. RF Frequency for Multiple IF Frequencies

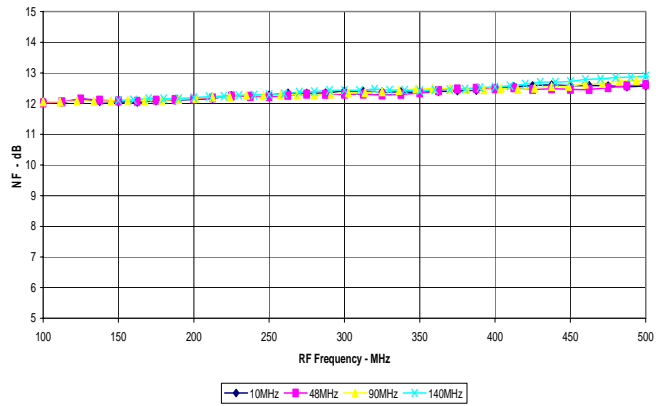


Figure 4. Single Sideband Noise Figure vs RF Frequency for Multiple IF Frequencies

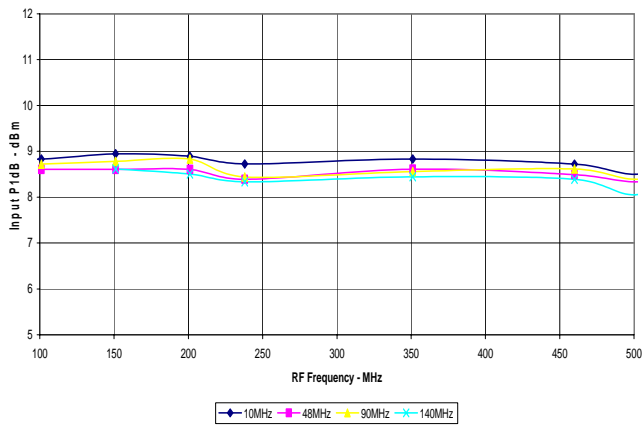


Figure 5. Input Compression Point vs RF Frequency for Multiple IF Frequencies

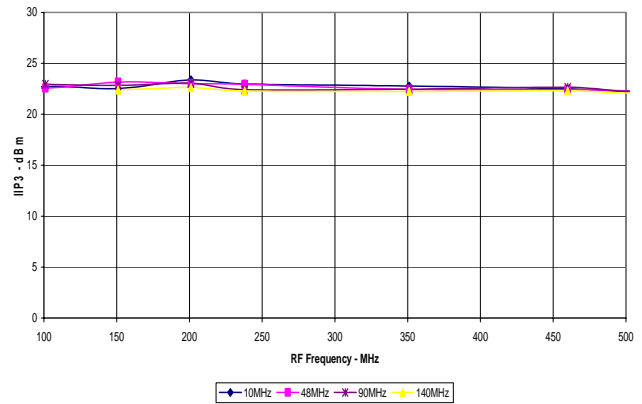
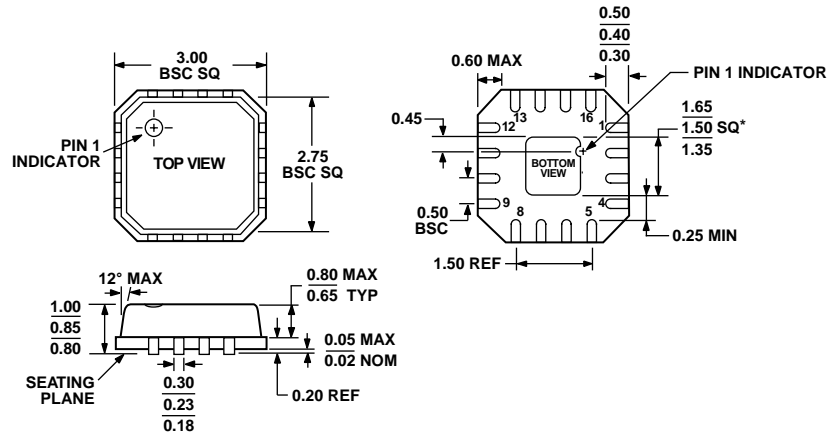


Figure 6. Input IP3 vs. RF Frequency for Multiple IF Frequencies

OUTLINE DIMENSIONS



* COMPLIANT TO JEDEC STANDARDS MO-220-VEED-2 EXCEPT FOR EXPOSED PAD DIMENSION

Figure 7. 16-Lead Lead Frame Chip Scale Package [LFCS]
3 mm × 3 mm Body (CP-16-3)
Dimensions in millimeters

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Datasheets for electronics components.